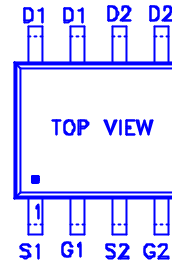
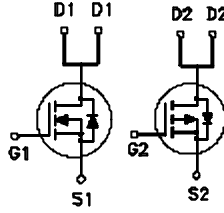


**PRODUCT SUMMARY**

	$V_{(BR)DSS}$	$R_{DS(ON)}$	$I_D$
N-Channel	60	58m	4.5A
P-Channel	-60	90m	-3.5A



G : GATE  
D : DRAIN  
S : SOURCE

**ABSOLUTE MAXIMUM RATINGS ( $T_C = 25\text{ }^\circ\text{C}$  Unless Otherwise Noted)**

PARAMETERS/TEST CONDITIONS		SYMBOL	N-Channel	P-Channel	UNITS
Drain-Source Voltage		$V_{DS}$	60	-60	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	$\pm 20$	V
Continuous Drain Current	$T_C = 25\text{ }^\circ\text{C}$	$I_D$	4.5	-3.5	A
	$T_C = 70\text{ }^\circ\text{C}$		4	-3	
Pulsed Drain Current <sup>1</sup>		$I_{DM}$	20	-20	
Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	$P_D$	2		W
	$T_C = 70\text{ }^\circ\text{C}$		1.3		
Junction & Storage Temperature Range		$T_j, T_{stg}$	-55 to 150		$^\circ\text{C}$
Lead Temperature ( $1/16''$ from case for 10 sec.)		$T_L$	275		

**THERMAL RESISTANCE RATINGS**

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient	$R_{\theta JA}$		62.5	$^\circ\text{C} / \text{W}$

<sup>1</sup>Pulse width limited by maximum junction temperature.

<sup>2</sup>Duty cycle  $\leq 1\%$

**ELECTRICAL CHARACTERISTICS ( $T_C = 25\text{ }^\circ\text{C}$ , Unless Otherwise Noted)**

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
<b>STATIC</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	N-Ch	60		V
		$V_{GS} = 0V, I_D = -250\mu A$	P-Ch	-60		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	N-Ch	1.0	1.5	2.5
		$V_{DS} = V_{GS}, I_D = -250\mu A$	P-Ch	-1.0	-1.5	-2.5
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 20V$	N-Ch			$\pm 100$
		$V_{DS} = 0V, V_{GS} = \pm 20V$	P-Ch			$\pm 100$

Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 48V, V_{GS} = 0V$	N-Ch		1	$\mu A$	
		$V_{DS} = -48V, V_{GS} = 0V$	P-Ch		-1		
		$V_{DS} = 40V, V_{GS} = 0V, T_J = 55^\circ C$	N-Ch		10		
		$V_{DS} = -40V, V_{GS} = 0V, T_J = 55^\circ C$	P-Ch		-10		
On-State Drain Current <sup>1</sup>	$I_{D(ON)}$	$V_{DS} = 5V, V_{GS} = 10V$	N-Ch	20		A	
		$V_{DS} = -5V, V_{GS} = -10V$	P-Ch	-20			
Drain-Source On-State Resistance <sup>1</sup>	$R_{DS(ON)}$	$V_{GS} = 4.5V, I_D = 4A$	N-Ch		55	85	m
		$V_{GS} = -4.5V, I_D = -3A$	P-Ch		100	135	
		$V_{GS} = 10V, I_D = 4.5A$	N-Ch		42	58	
		$V_{GS} = -10V, I_D = -3.5A$	P-Ch		70	90	
Forward Transconductance <sup>1</sup>	$g_{fs}$	$V_{DS} = 10V, I_D = 4.5A$	N-Ch		14	S	
		$V_{DS} = -5V, I_D = -3.5A$	P-Ch		9		

**DYNAMIC**

Input Capacitance	$C_{iss}$		N-Ch		650		$pF$
		N-Channel	P-Ch		630		
Output Capacitance	$C_{oss}$	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$	N-Ch		80		$pF$
		P-Channel	P-Ch		81		
Reverse Transfer Capacitance	$C_{rss}$	$V_{GS} = 0V, V_{DS} = -30V, f = 1MHz$	N-Ch		35		$pF$
			P-Ch		33		
Total Gate Charge <sup>2</sup>	$Q_g$	N-Channel	N-Ch		12	16	nC
		$V_{DS} = 0.5V_{(BR)DSS}, V_{GS} = 10V,$	P-Ch		11	15	
		$I_D = 4.5A$	N-Ch		2.4		
		P-Channel	P-Ch		2.1		
Gate-Source Charge <sup>2</sup>	$Q_{gs}$						nC
		$V_{DS} = 0.5V_{(BR)DSS}, V_{GS} = -10V,$	N-Ch		2.6		
		$I_D = -3.5A$	P-Ch		2.5		
Turn-On Delay Time <sup>2</sup>	$t_{d(on)}$	N-Channel	N-Ch		11	20	nS
			P-Ch		6	13	
		$V_{DD} = 30V$	N-Ch		8	18	
		$I_D \cong 1A, V_{GS} = 10V, R_{GEN} = 6$	P-Ch		8	18	
		P-Channel	N-Ch		19	35	
			P-Ch		17	31	
		$V_{DD} = -30V$	N-Ch		6	15	
		$I_D \cong -1A, V_{GS} = -10V, R_{GEN} = 6$	P-Ch		11	20	

**SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T<sub>C</sub> = 25 °C)**

Continuous Current	I <sub>S</sub>		N-Ch			1.3	A
			P-Ch			-1.3	
Pulsed Current <sup>3</sup>	I <sub>SM</sub>		N-Ch			2.6	A
			P-Ch			-2.6	
Forward Voltage <sup>1</sup>	V <sub>SD</sub>	I <sub>F</sub> = I <sub>S</sub> A, V <sub>GS</sub> = 0V	N-Ch			1	V
		I <sub>F</sub> = I <sub>S</sub> A, V <sub>GS</sub> = 0V	P-Ch			-1	

<sup>1</sup>Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

<sup>2</sup>Independent of operating temperature.

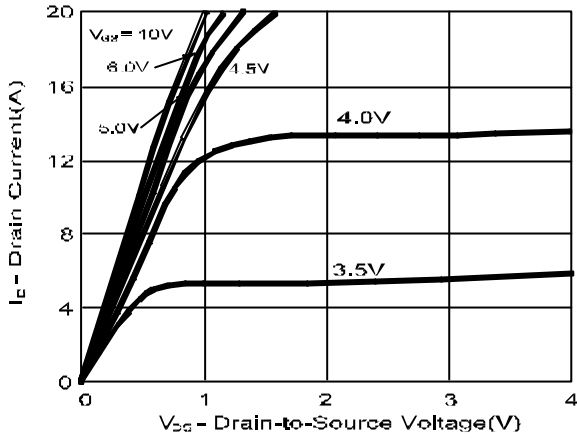
<sup>3</sup>Pulse width limited by maximum junction temperature.

**REMARK: THE PRODUCT MARKED WITH “P5806NVG”, DATE CODE or LOT #**

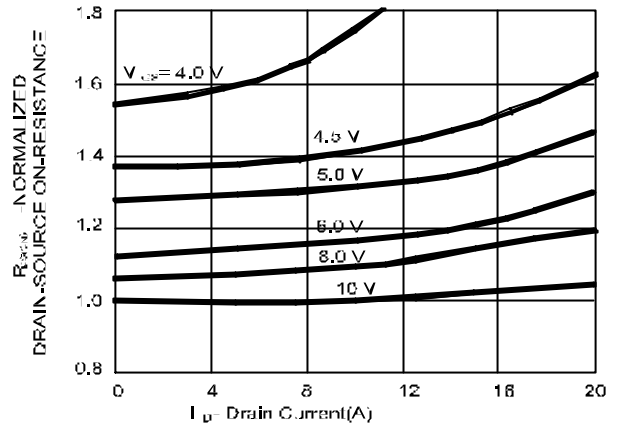
**Orders for parts with Lead-Free plating can be placed using the PXXXXXXG parts name.**

**N-CHANNEL**

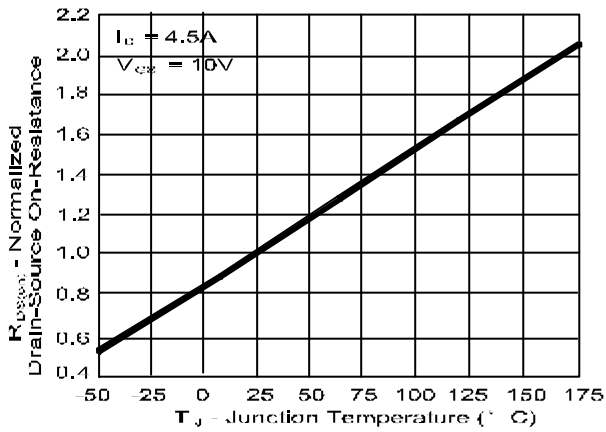
**On-Region Characteristics**



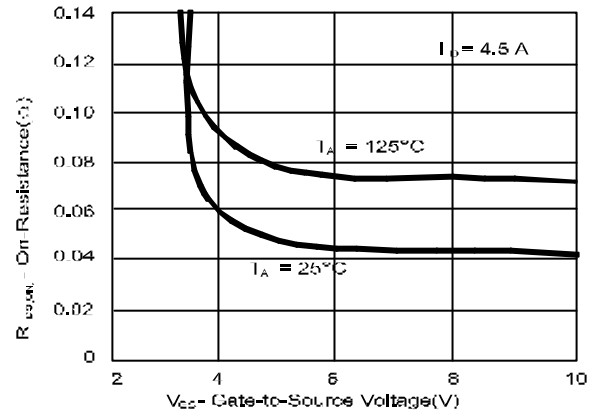
**On-Resistance Variation with Drain Current and Gate Voltage**



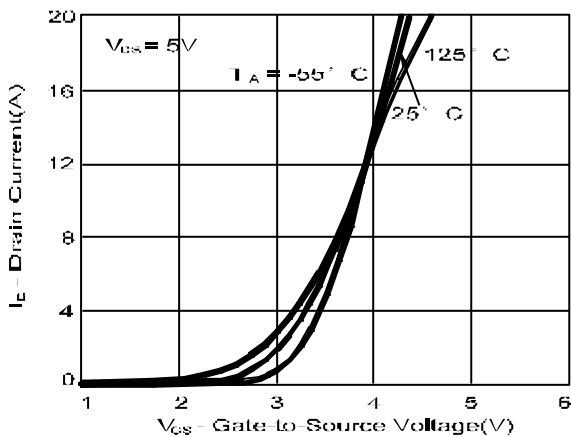
**On-Resistance Variation with Temperature**



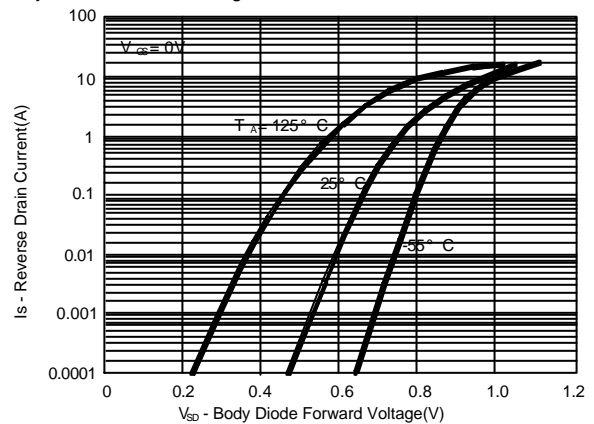
**On-Resistance Variation with Gate-to-Source Voltage**

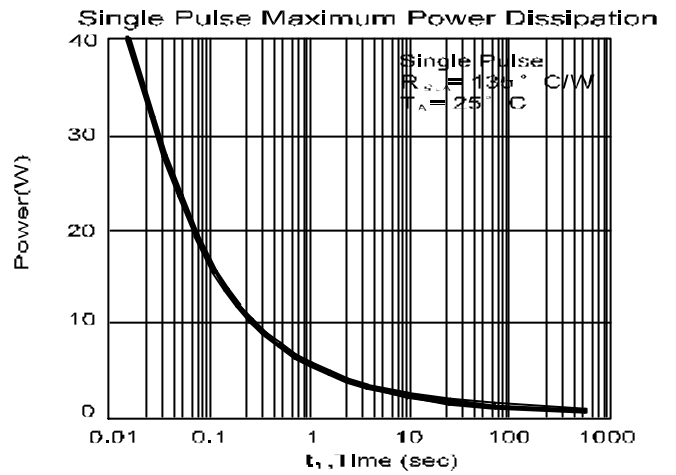
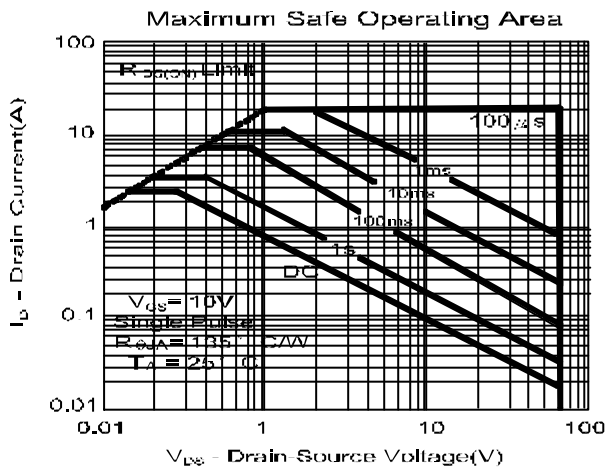
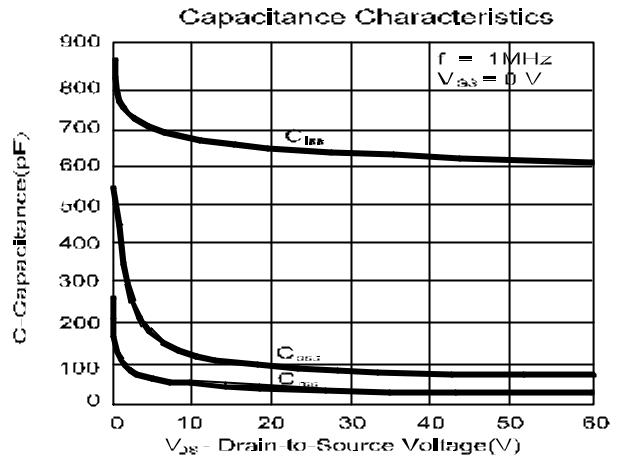
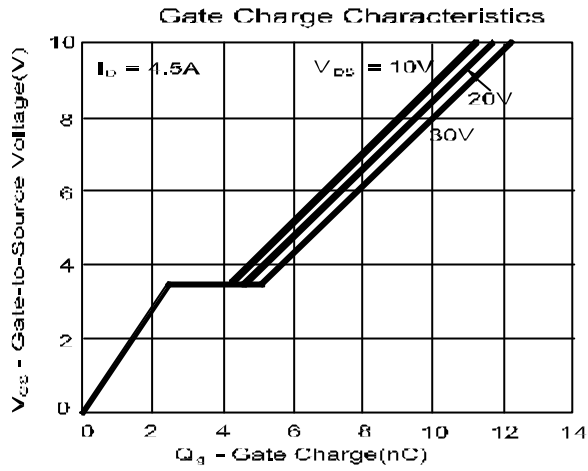


**Transfer Characteristics**



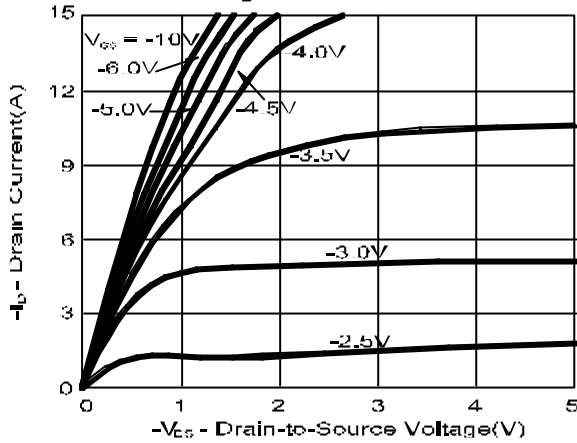
**Body Diode Forward Voltage Variation with Source Current and Temperature**



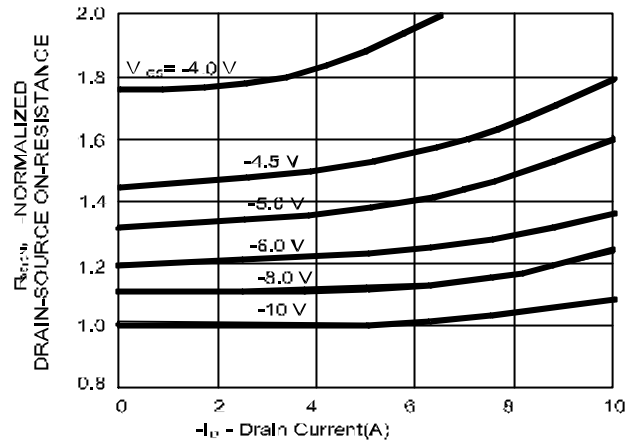


**P-CHANNEL**

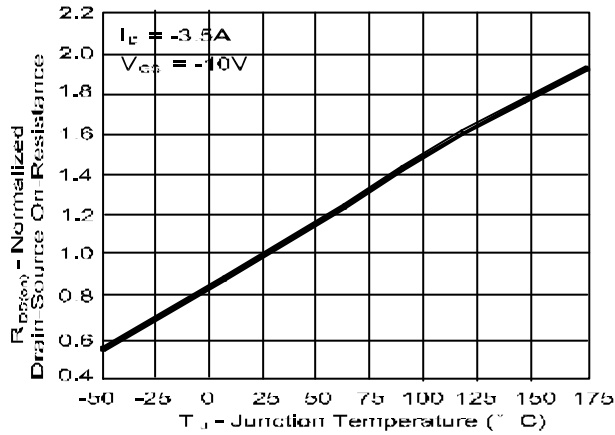
**On-Region Characteristics**



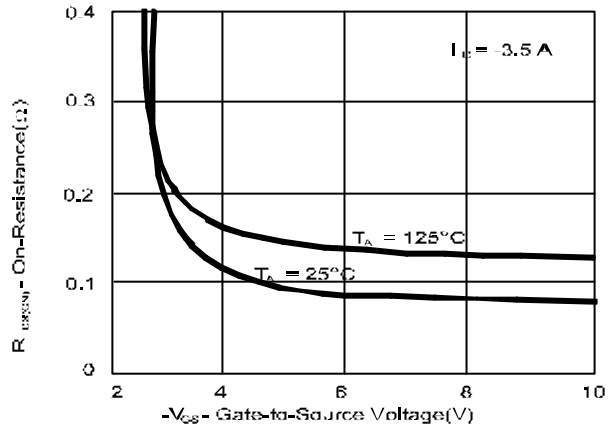
**On-Resistance Variation with Drain Current and Gate Voltage**



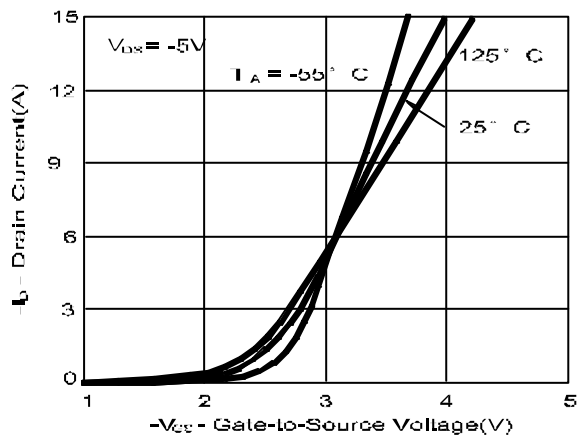
**On-Resistance Variation with Temperature**



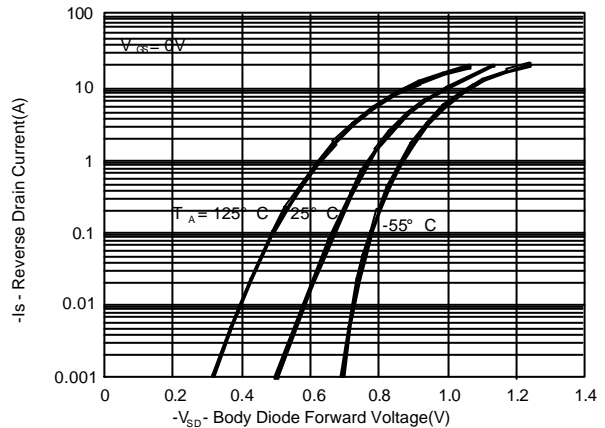
**On-Resistance Variation with Gate-to-Source Voltage**

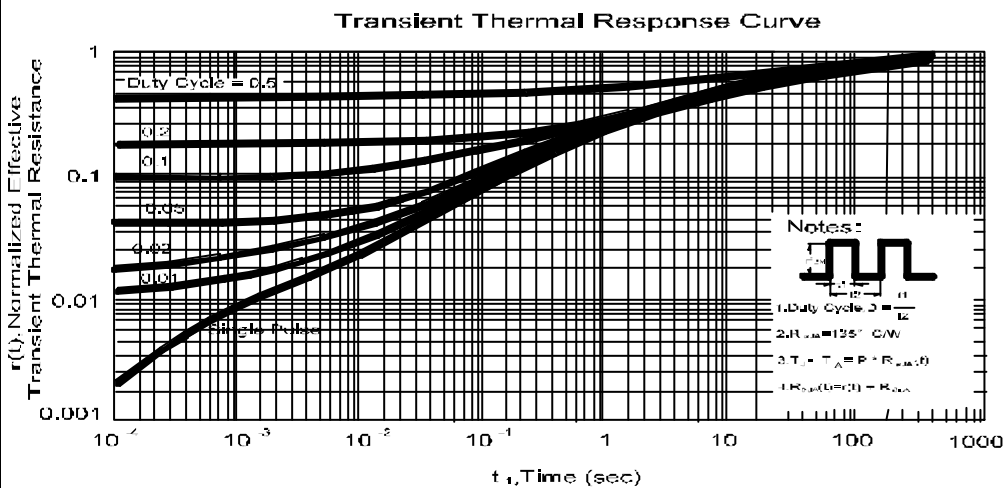
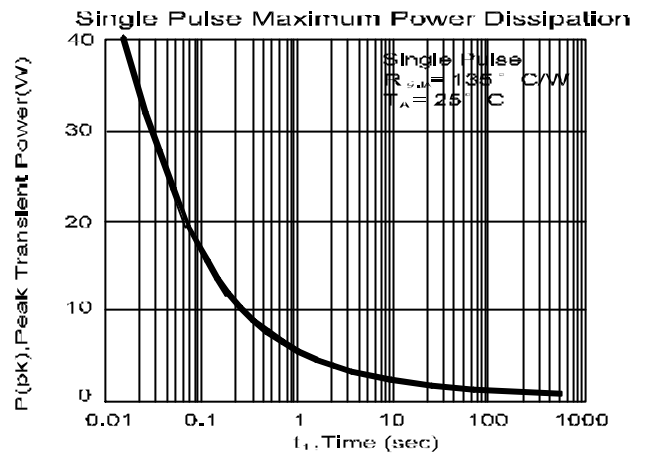
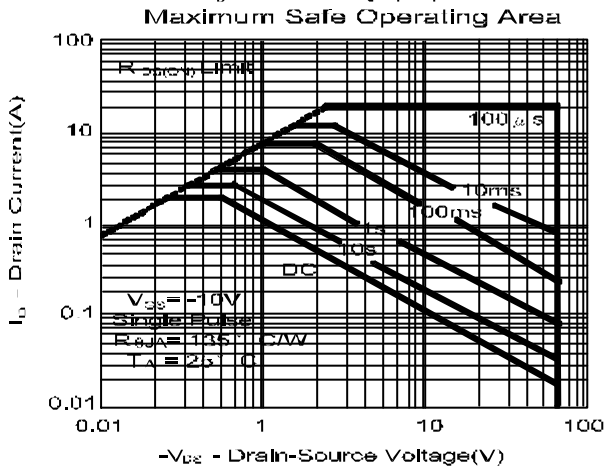
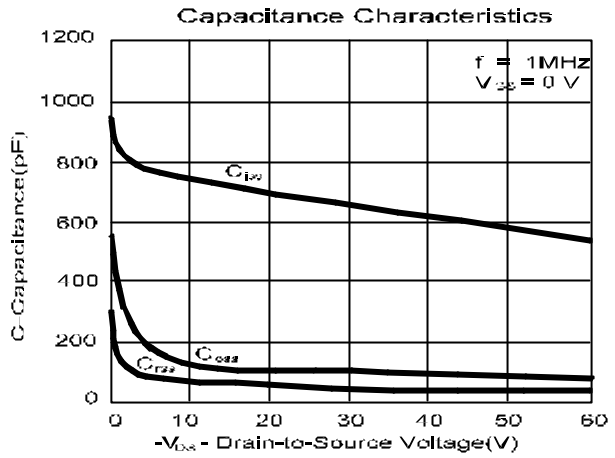
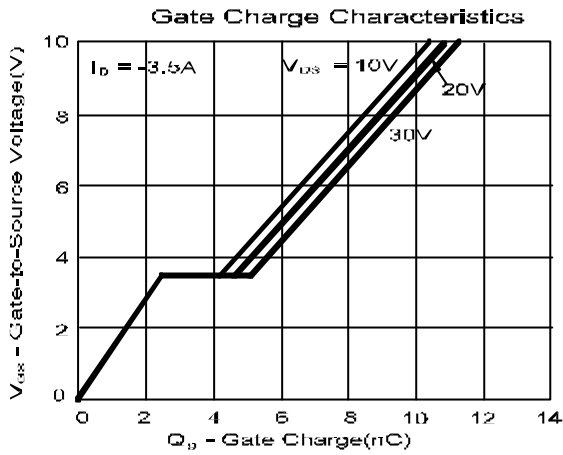


**Transfer Characteristics**



**Body Diode Forward Voltage Variation with Source Current and Temperature**





**SOIC-8(D) MECHANICAL DATA**

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.8	4.9	5.0	H	0.5	0.715	0.83
B	3.8	3.9	4.0	I	0.18	0.254	0.25
C	5.8	6.0	6.2	J		0.22	
D	0.38	0.445	0.51	K	0°	4°	8°
E		1.27		L			
F	1.35	1.55	1.75	M			
G	0.1	0.175	0.25	N			

